

# Navitas Delivers AI Server Power: GaN & SiC Hybrid 4.5 kW

*Kevin Wang*  
*Sr Director Sales and Taiwan Country Manager*

**21<sup>st</sup> March 2024**



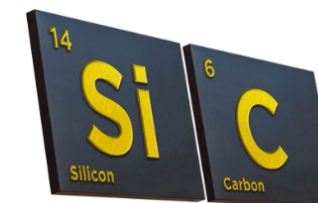
# 10 YEARS





**GaNFast™**

**GeneSiC™**



Up to  
**20x**  
Faster  
Switching<sup>(1)</sup>

Up to  
**3x**  
Smaller &  
Lighter<sup>(1)</sup>

Up to  
**40%**  
Energy  
Savings<sup>(1)</sup>

Up to  
**3x**  
Higher  
Power Density<sup>(1)</sup>

Up to  
**3x**  
Faster  
Charging<sup>(1)</sup>

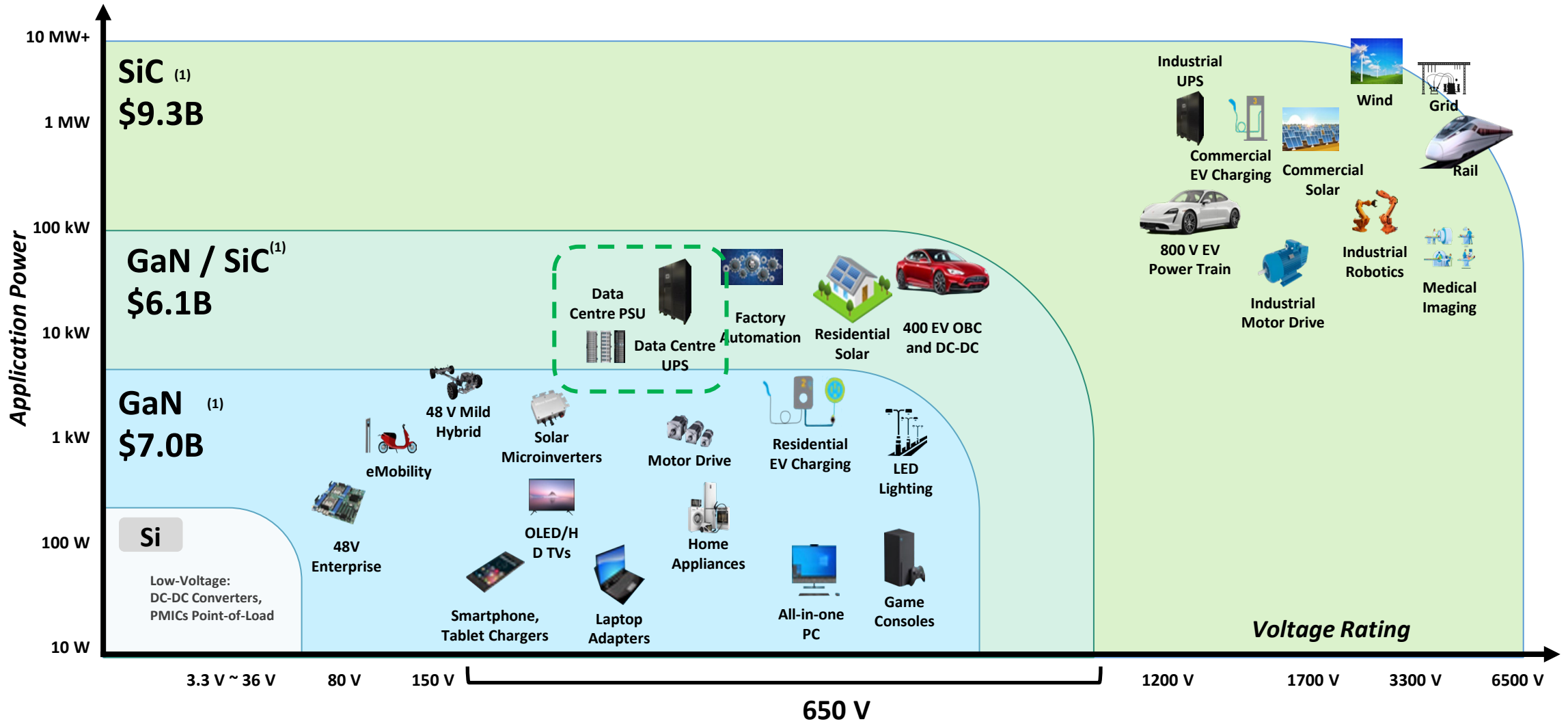
Up to  
**25%**  
Lower  
System Cost<sup>(2)</sup>



**GaN and SiC replacing Si in next-generation power applications**

1. Statistical data is based on Navitas estimates of GaN-based systems compared to Si-based estimates in the 2024-2025 timeframe. Based on Navitas measurements of select GaN-based mobile wall chargers compared to Si-based chargers with similar output power, incl. 2019 study of 65W fast chargers, 2022 customer statement re 2.7 kW data center AC-DC  
2. Navitas estimates based on customer feedback as the expected system cost saving overtime as of April 2023

# \$22B+ GaN & SiC 'Pure-Play' Opportunity <sup>(1)</sup>






Notes: Axes not to scale

1. Based on internal company estimates, Navitas believes that the potential market opportunity in 2026 is \$22B+ for GaN and SiC, replacing certain of the silicon market share

2. Per Yole Development, 2024-2024 estimated market revenue

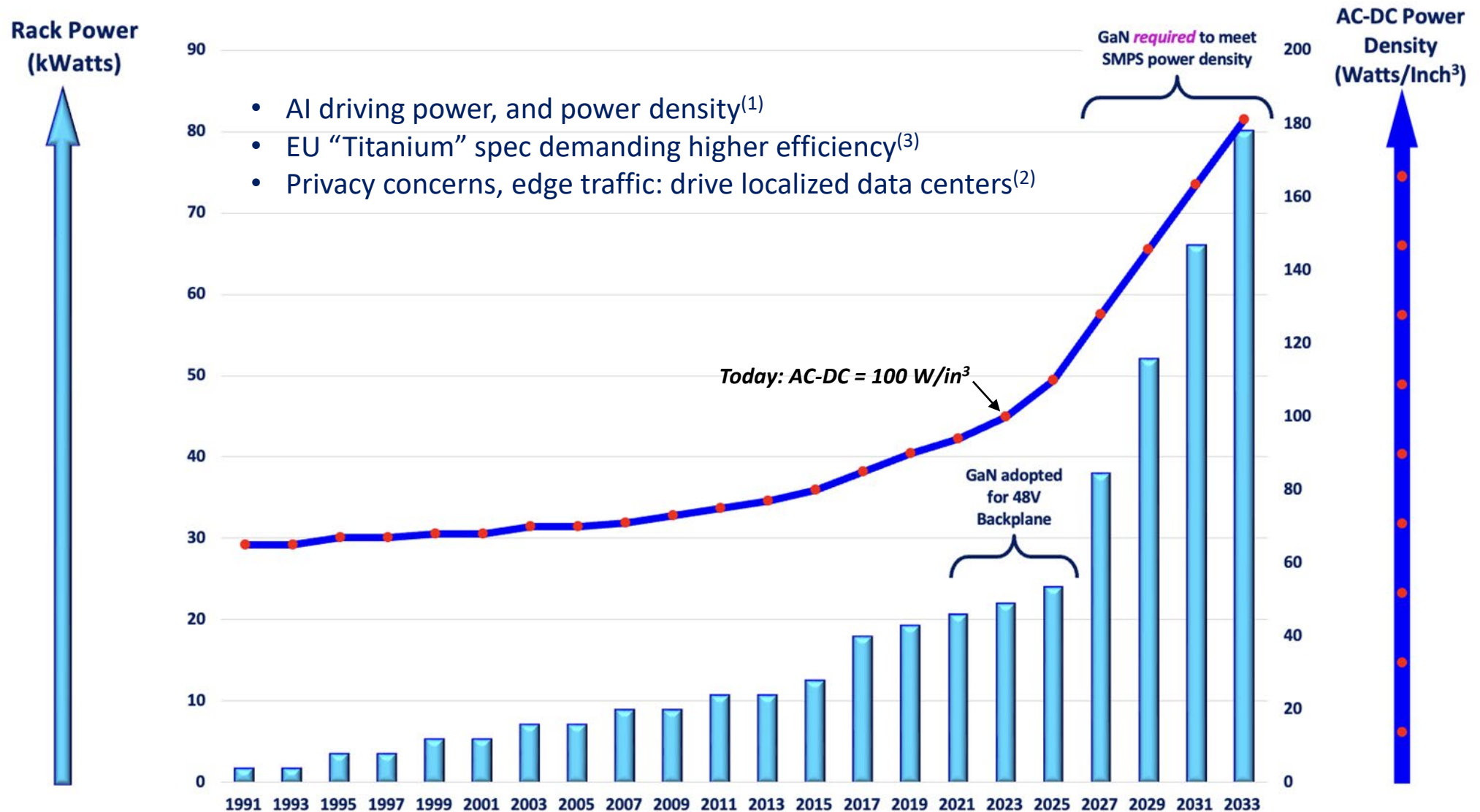
# The Efficiency Challenge: “Titanium Plus”

80 Plus test type	Icon	115 V internal non-redundant				230 V internal redundant				230 V EU internal non-redundant			
		10%	20%	50%	100%	10%	20%	50%	100%	10%	20%	50%	100%
80 Plus Gold			87%	90%	87%		88%	92%	88%		90%	92%	89%
80 Plus Platinum			90%	92%	89%		90%	94%	91%		92%	94%	90%
80 Plus Titanium		90%	92%	94%	90%	90%	94%	96%	91%	90%	94%	96%	94%



European Union: [‘Directive 2009/125/EC, 2019 Annex’](#)

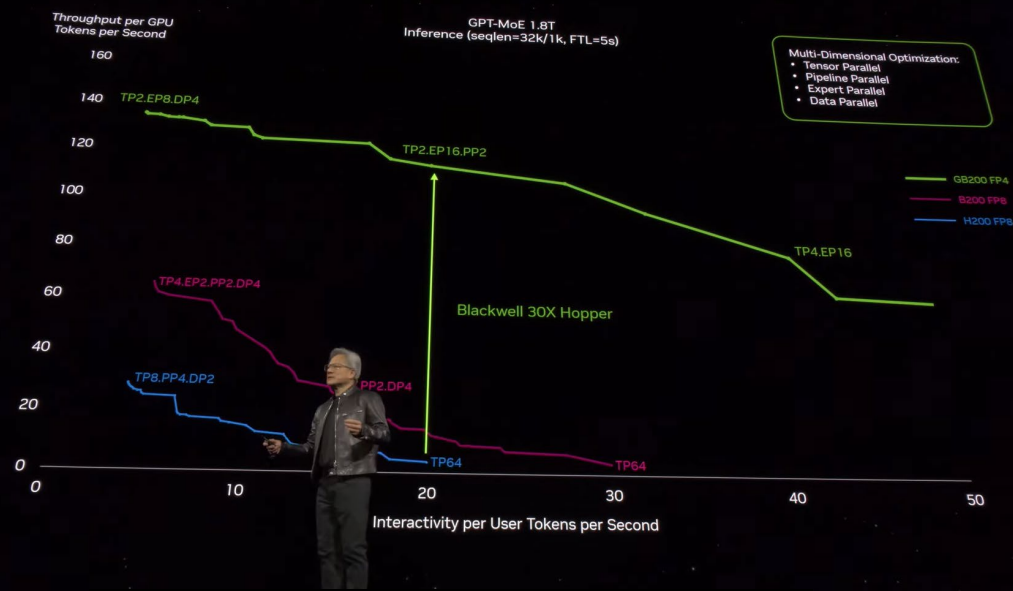
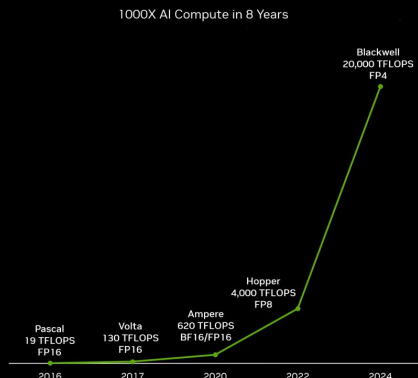
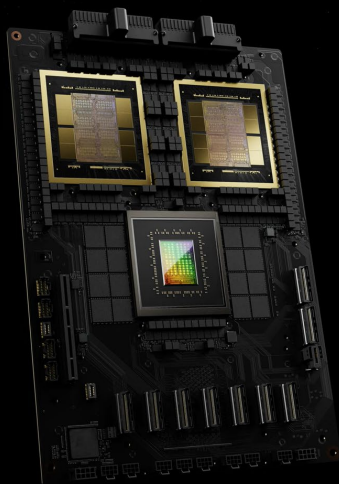
# The Power Challenge #1: Data Center Power



- AI driving power, and power density<sup>(1)</sup>
- EU “Titanium” spec demanding higher efficiency<sup>(3)</sup>
- Privacy concerns, edge traffic: drive localized data centers<sup>(2)</sup>

1. Cerebras white paper / website  
 2. TD Cowen, per “AI to drive data center investments”, LightReading.com, 4-26-23  
 3. European Union ‘Directive 2009/125/EC, 2019 Annex’, power supplies must be >96% efficiency peak, as of 1-1-23

# The Power Challenge #2: NVIDIA AI GPUs



Train GPT-MoE-1.8T in 90 Days


Blackwell GB200 NVL72  
2000 GPUs | 4MW

Blackwell processes 30x more tokens/s and only 1/4 the power of Grace Hopper but still 2,000W per GPU and >100kW per rack



## *AI Power Roadmap*

**3,200W - 4,500W - 10,000W**



**Navitas**  
*Titanium Plus*



# GaNSafe™

*The World's Safest GaN*

 Navitas



2 kV ESD



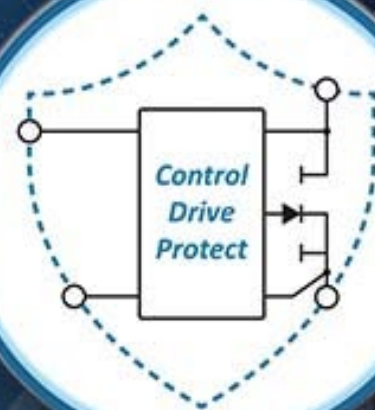
Easy EMI



High-Speed  
Short-Circuit Protection



800 V  
max



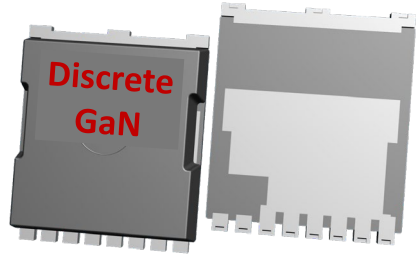
Robust  
Operation



Easy Cooling

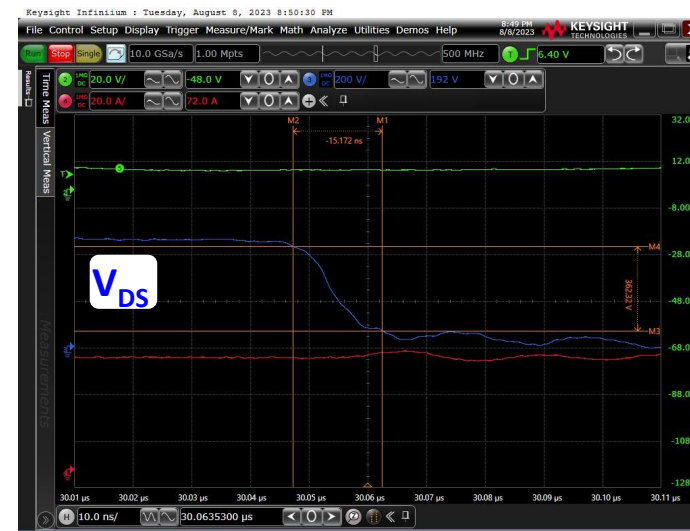
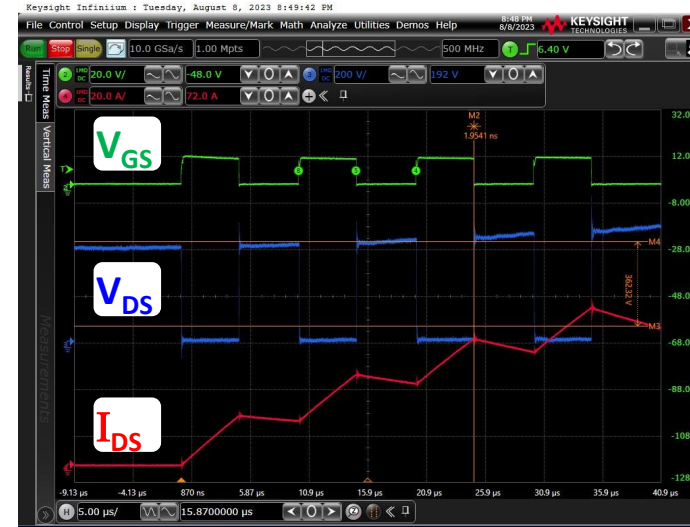
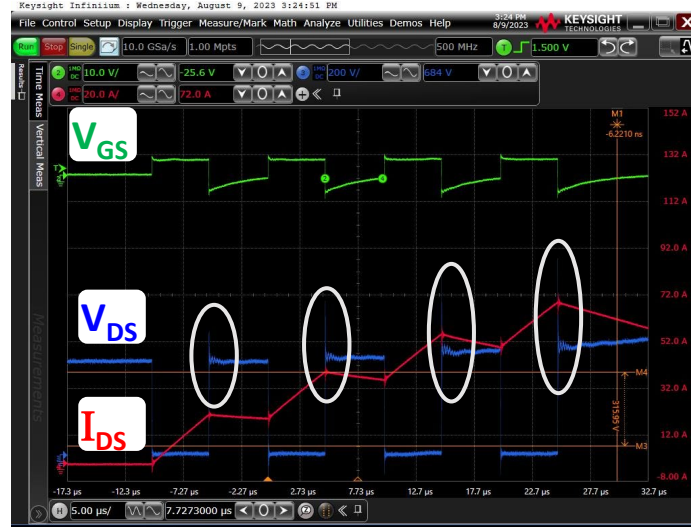
# GaN Safe Reliability: Double-Pulse Test

- Double-pulse test:  
400 V, 30 A,  $R_{SERIES} = 11\text{ m}\Omega$



**Discrete GaN**  
42 mΩ max

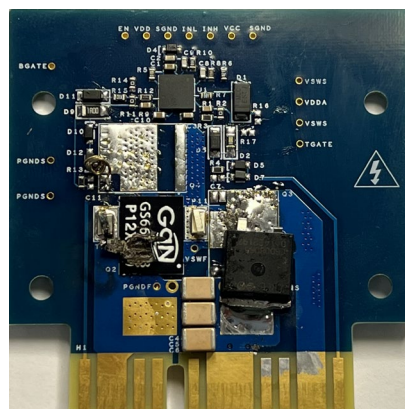
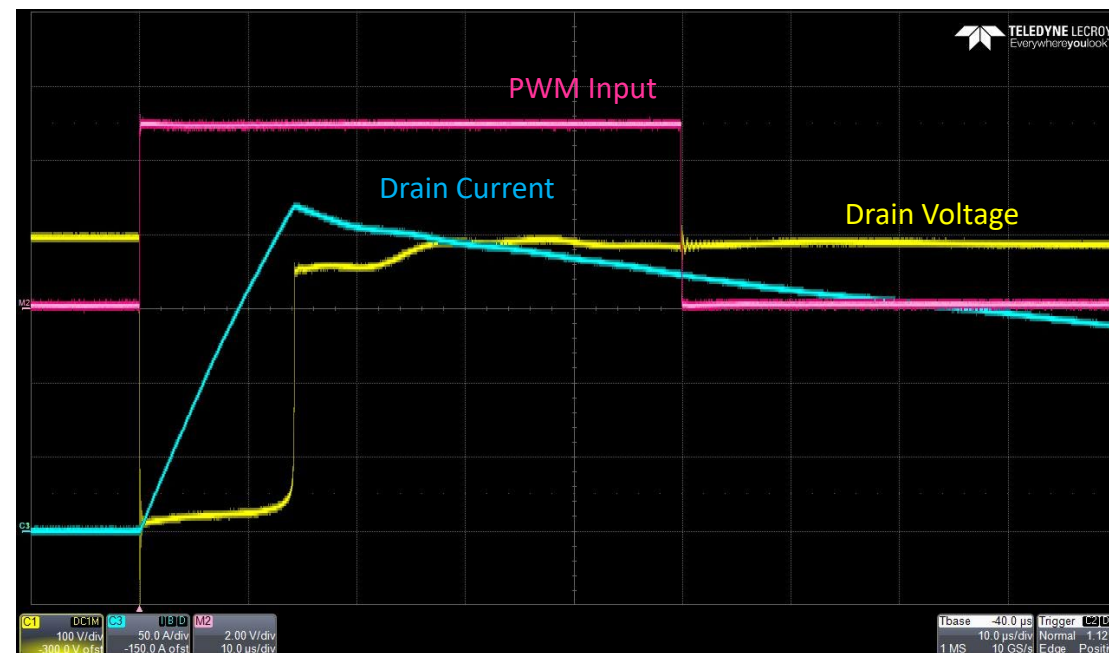
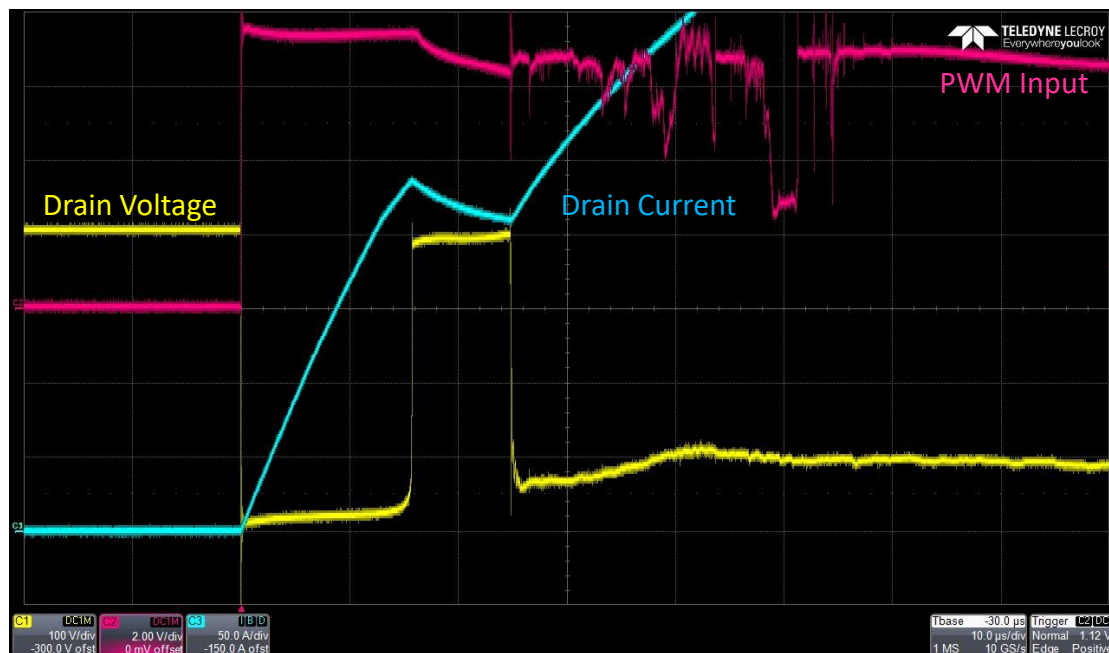
**Significant spikes**  
**Excessive turn-ON ringing**  
**250 V undershoot**



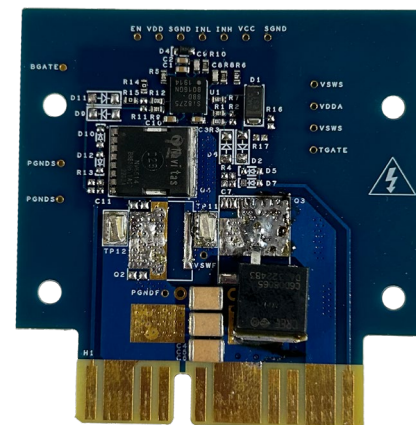
**GaN Safe™**  
45 mΩ max (NV6513)

**No voltage spikes**  
**No ringing**  
**No undershoot**



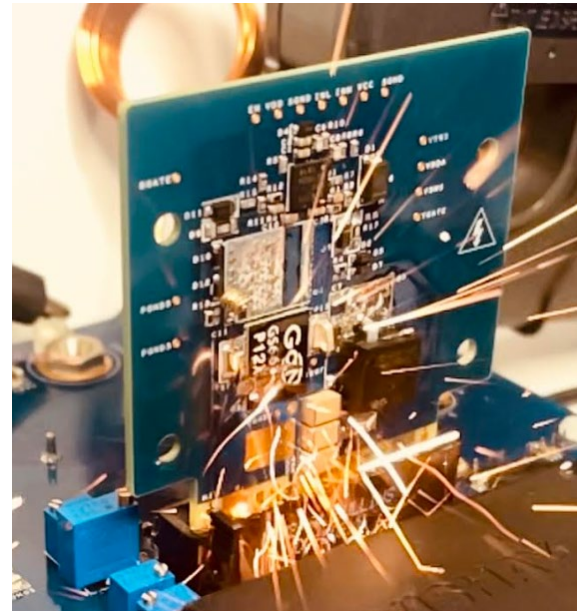
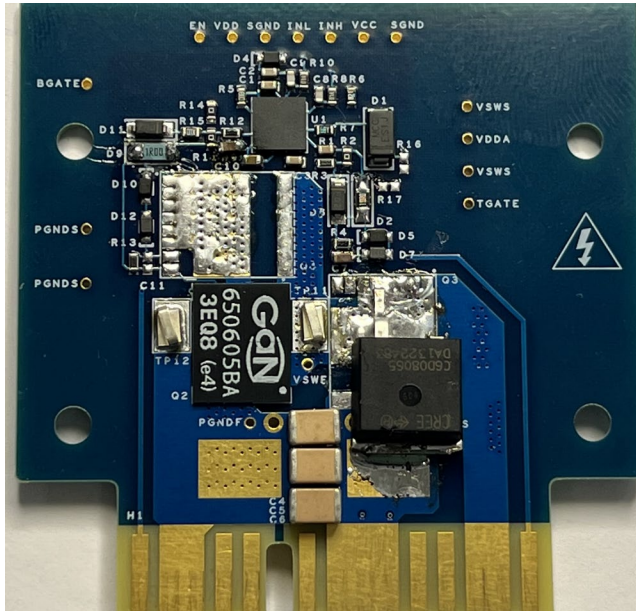


- Company X GaN discrete
- 650 V, 25 m $\Omega$  typ
- **Fails short**



- Navitas GaNSafe
- 650 V, 25 m $\Omega$  max (NV6514)
- **Survives short-circuit**

- Repeatabile issue



Up to 6.5 kV

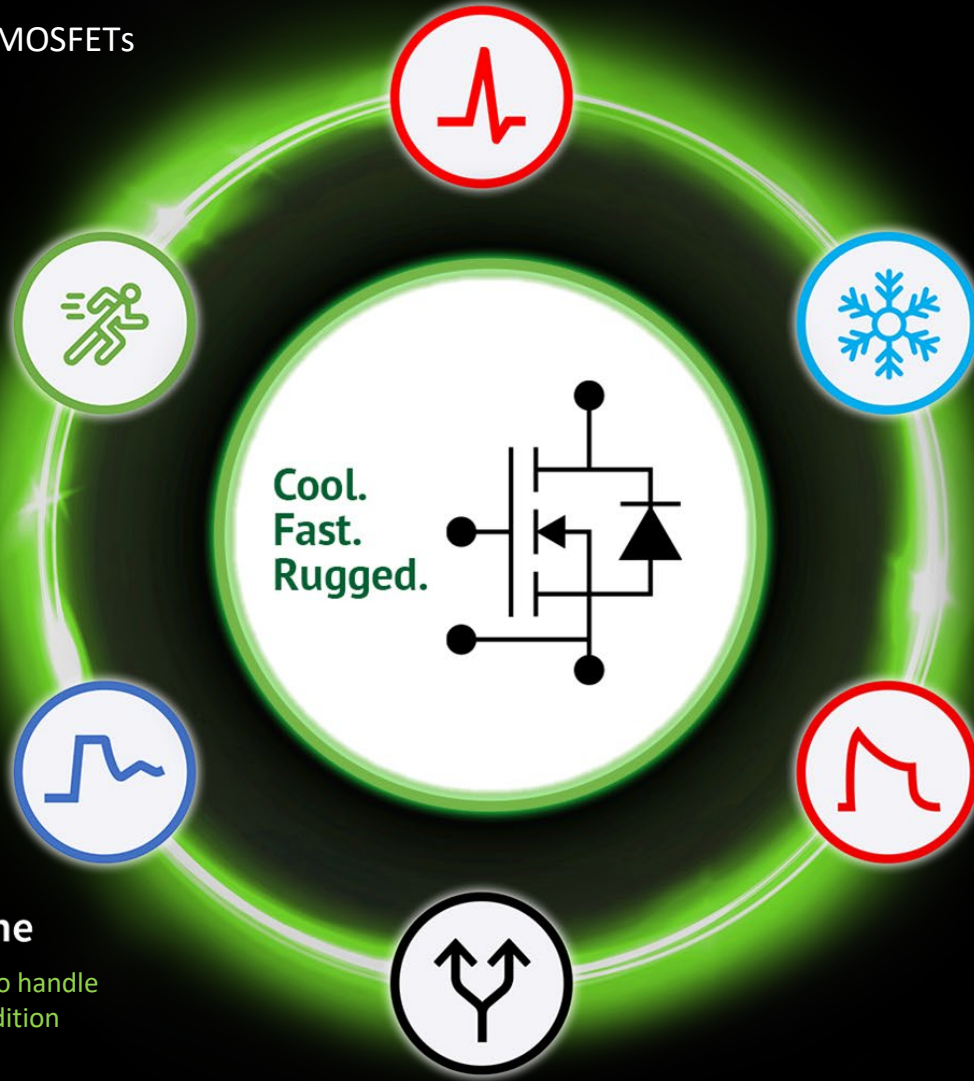
Largest range of SiC FETs & diodes  
(650 V to 6.5 kV)

**Fast Switching**

Highest efficiency hard-switch, soft-switch  
(Lowest  $E_{ON}$ ,  $E_{OFF}$ ,  $E_{ZVS}$  losses)

**Cool Operation**

Lowest  $R_{DS(ON)}$  at high temperature  
(25% lower than industry typical)



**Cool.  
Fast.  
Rugged.**

**100%-Tested Robust Avalanche**

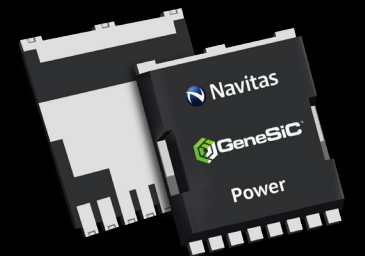
Highest published capability to handle excess energy in fault condition

**Long Short-Circuit Withstand Time**

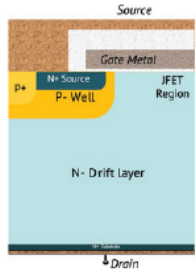
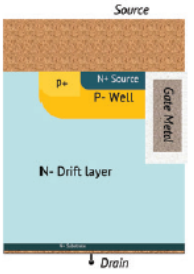
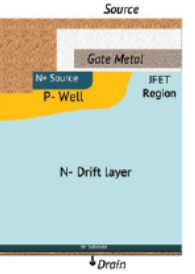
World-class survival duration in fault condition

**High-Power Paralleling**

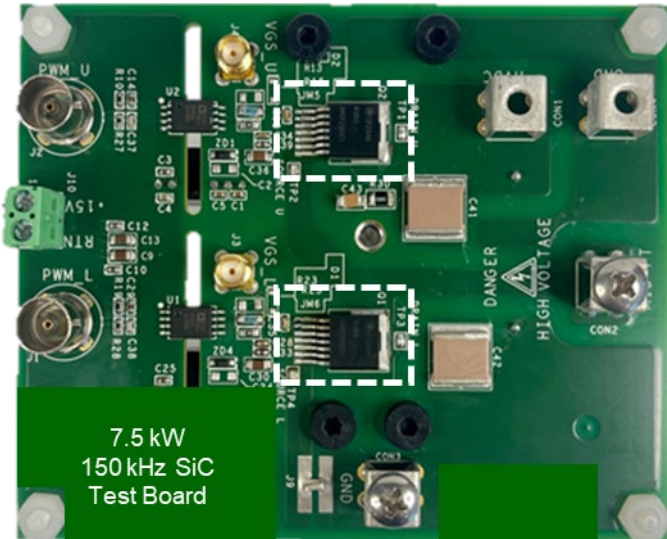
Matching currents  
(Stable  $V_{TH}$ )



# Trench-Assisted Planar Gate – No Compromise

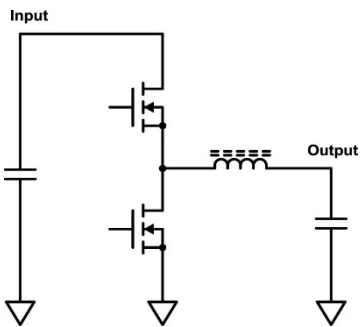
	 <p><b>Planar</b></p>	 <p><b>Trench</b></p>	 <p><b>GeneSiC</b></p>
<b>Manufacturability</b>	<ul style="list-style-type: none"> <li>» Repeatable</li> <li>» High yield</li> <li>» Low cost</li> </ul>	<ul style="list-style-type: none"> <li>» Inconsistent trench etch</li> <li>» Lower yields</li> <li>» High cost</li> </ul>	<ul style="list-style-type: none"> <li>» Repeatable</li> <li>» High yield</li> <li>» Low cost</li> </ul>
<b>Performance</b>	<ul style="list-style-type: none"> <li>» High <math>R_{DS(ON)}</math> / area</li> <li>» Slow switching</li> <li>» High <math>R_{DS(ON)}</math> / <math>\Delta</math> temp</li> </ul>	<ul style="list-style-type: none"> <li>» Lower <math>R_{DS(ON)}</math> / area</li> <li>» Faster switching</li> <li>» High <math>R_{DS(ON)}</math> / <math>\Delta</math> temp</li> </ul>	<ul style="list-style-type: none"> <li>» Lower <math>R_{DS(ON)}</math> / area</li> <li>» Fastest switching</li> <li>» Lowest <math>R_{DS(ON)}</math> / <math>\Delta</math> temp</li> </ul>
<b>Reliability</b>	<ul style="list-style-type: none"> <li>» Rugged gate oxide (stable <math>V_{TH}</math>)</li> </ul>	<ul style="list-style-type: none"> <li>» Failures due to non-uniform gate oxide</li> <li>» Lower short-circuit capability</li> </ul>	<ul style="list-style-type: none"> <li>» Highest 100% tested avalanche</li> <li>» Long short-circuit withstand time</li> <li>» Rugged gate oxide (stable <math>V_{TH}</math>)</li> </ul>

# Faster, Cooler, Longer Lifetime

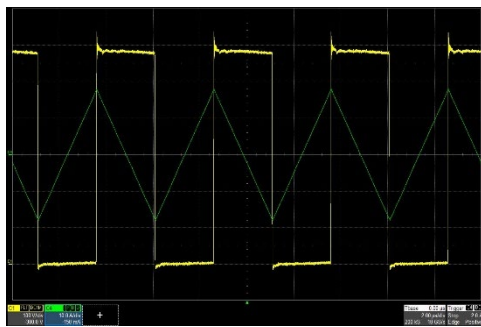


Test Board

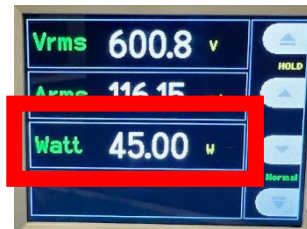
- GeneSiC trench-assisted planar FET vs. Competitor SiC FET
  - 1,200 V, 40 mΩ, D2pak in half-bridge
  - Represents 7.5 kW DC-DC converter (e.g. data center, EV)
  - 150 kHz switching = ~10x faster than Si IGBT example
- **>80% energy savings (>3,000 kWh/yr) vs Si IGBTs**  
**-25°C cooler = 3x longer life vs other SiC**  
**(reduced maintenance / repair costs)**



Test Circuit  
(1-phase of 3-phase motor drive)



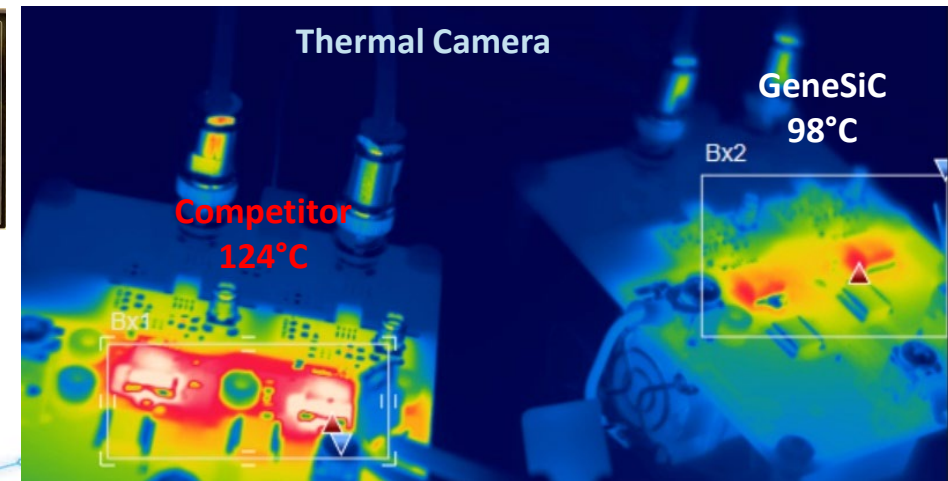
Switching Waveforms  
(40 A pk-pk, 20 A turn-off)



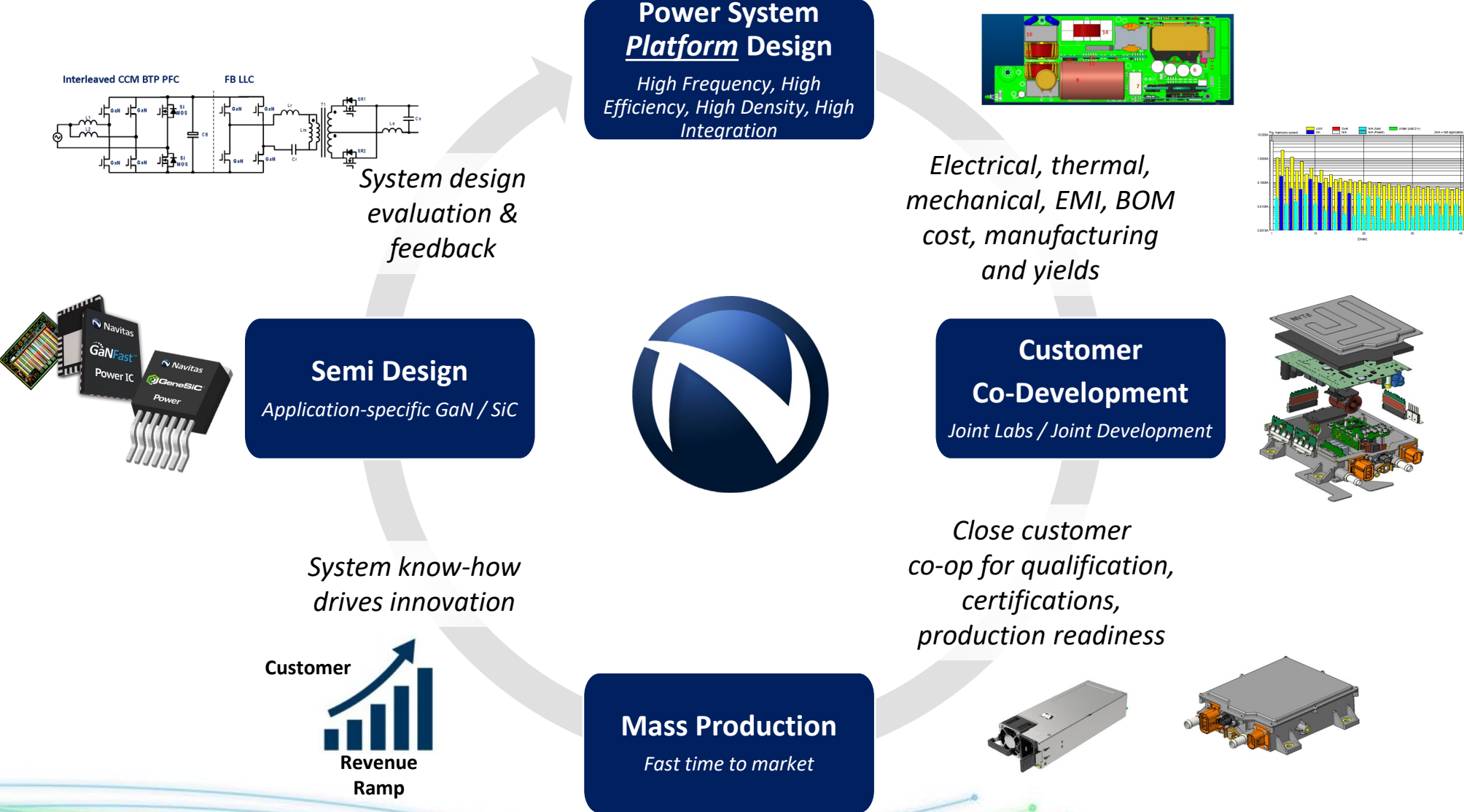
Competitor SiC  
45 W system loss



GeneSiC  
40 W system loss  
-30% SiC loss



# Faster Time-to-Market: Unique System Design Centers





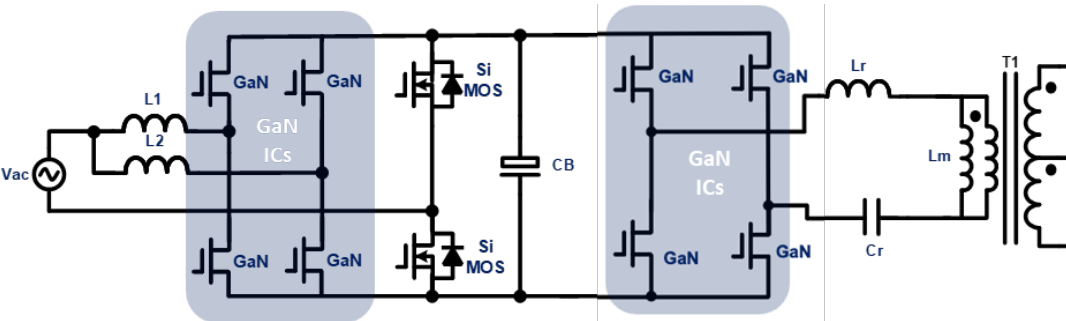
# NVTS 3.2 kW Sets New Density, Efficiency Levels

- Data center AC-DC 12 V high performance PSU
- CRPS185 form factor

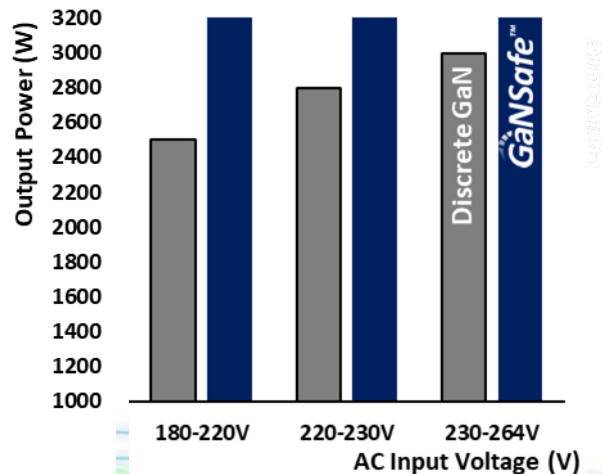


Power	3,000 W	3,200 W
PFC	8 x 32 mΩ GaN	4 x 60 mΩ SiC
DC-DC	4 x 32 mΩ GaN	4 x 45 mΩ GaN
Total	12 x GaNpx™ 	8 x TOLL 

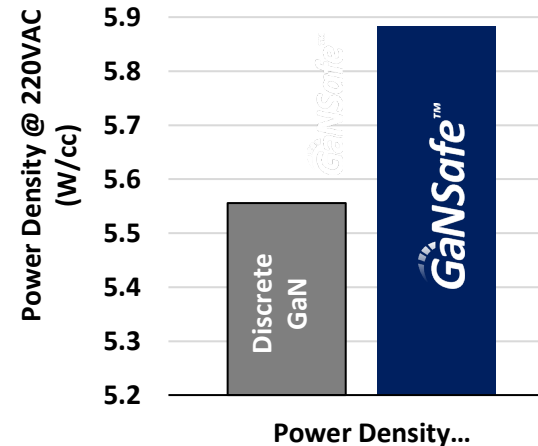
**Navitas**  
33% fewer power components



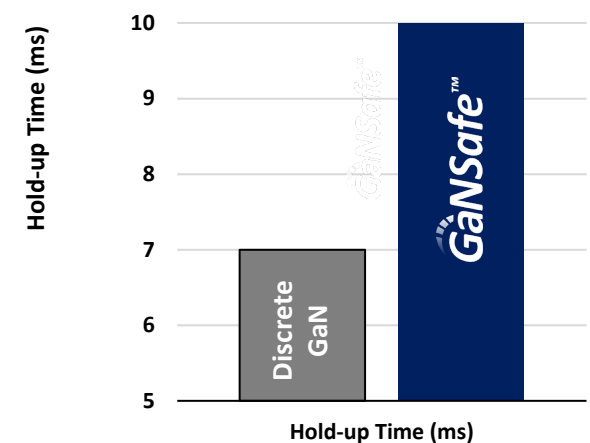
**Navitas** True 3,200 W CRPS185



**Navitas** ~100 W/in<sup>3</sup>

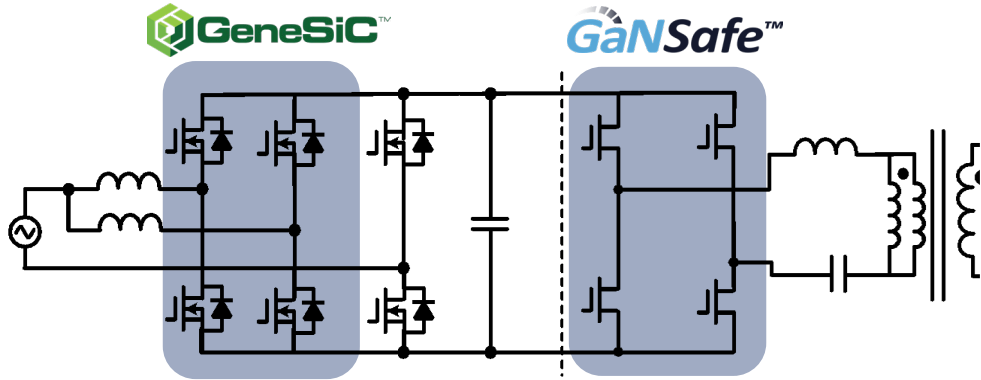


**Navitas** +40% Hold-up



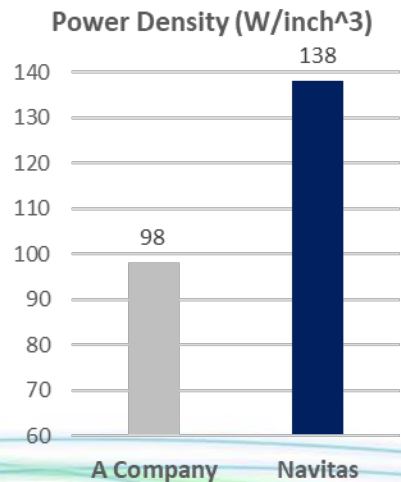
# NVTS 4.5 kW AI Server Power

- Data center AC-DC 54 V AI/GPU Server PSU
- CRPS185 form factor

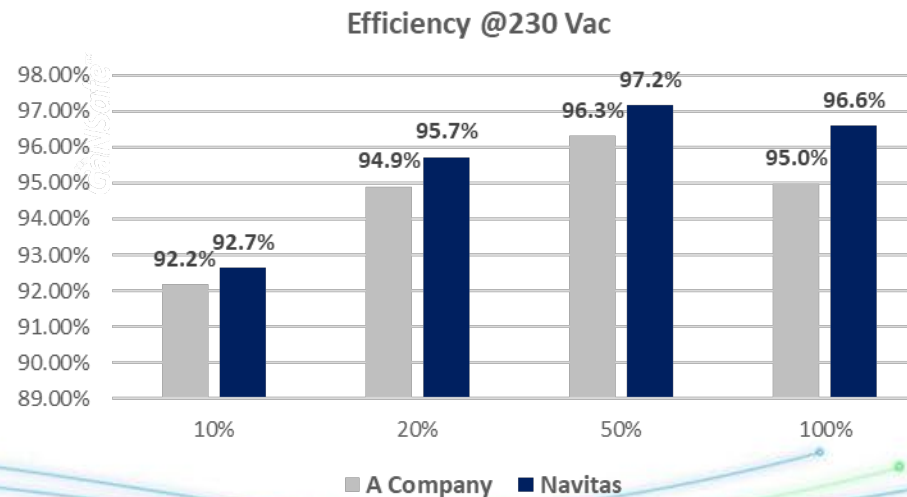


Company	A Company	Navitas
Power	3,200 W	4,500 W
DC-DC	<150 kHz Si/SiC	300 kHz GaN
PD	98 W/in <sup>3</sup>	138 W/in <sup>3</sup>
Eff	~96.3%	>97%

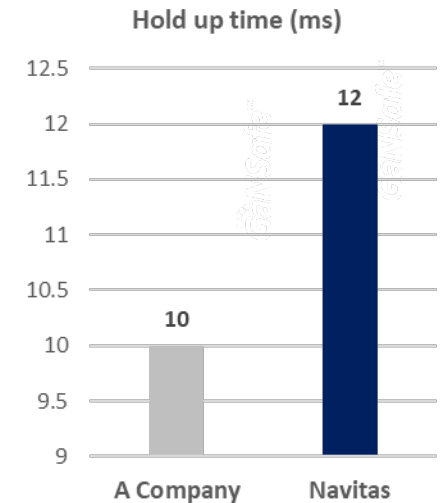
## Navitas +40% Power Density



## Navitas >97% Efficiency

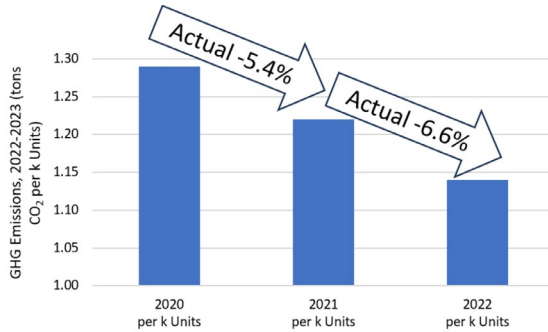


## Navitas +20% Hold-up

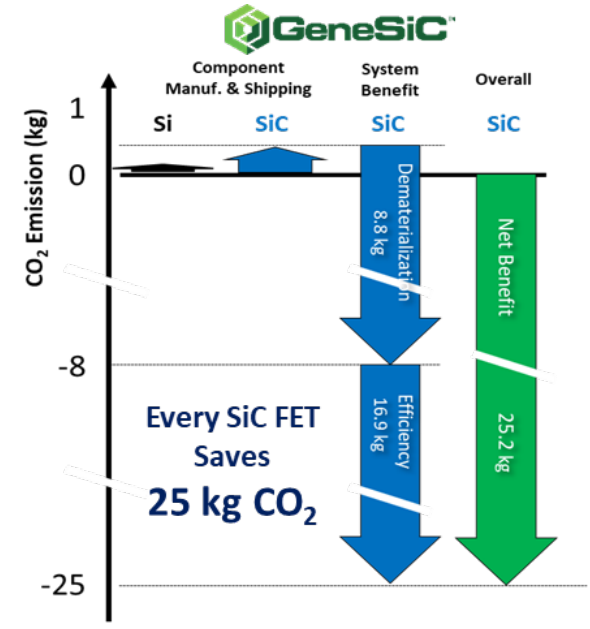
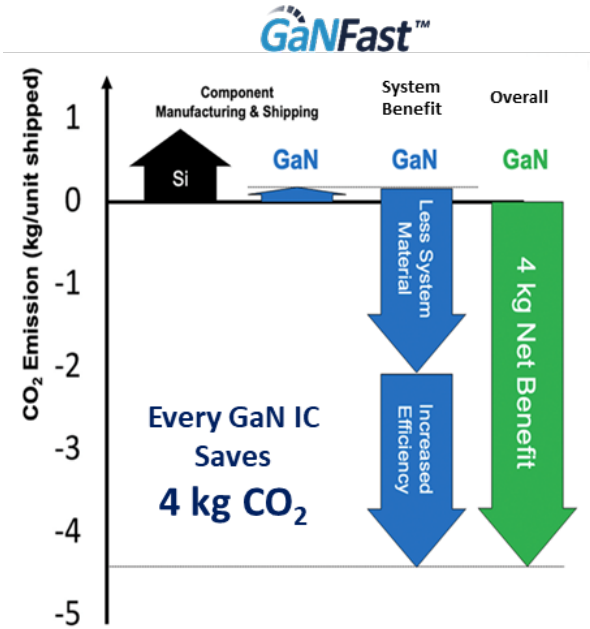
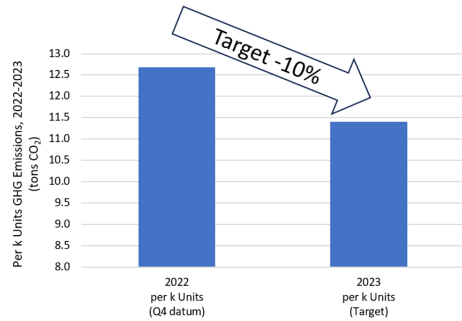


# Accelerating Sustainability

## Navitas Corporate GHG Scope 2, 3 (GaN only)



## Navitas Corporate GHG Scope 2, 3 (GaN + SiC)



Feb '22 World's first GaN Sustainability Report



May '22 World's first semiconductor Company certified CarbonNeutral®



Aug '22 First 100,000 tons CO<sub>2</sub> saved [Nov'23 over 200,000 tons]



Oct '22 Recognized as Industry-Leading Sustainability Company



Nov '23 Consolidated GaN + SiC Sustainability Report

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*Sr Director Sales and Taiwan Country Manager*

**21<sup>st</sup> March 2024**

